ELECTRONICS, INC.
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NTE5864 thru NTE5889
Silicon Power Rectifier Diode, 25 Amp

Description:

The NTE5864 through NTE5889 are silicon power rectifier diodes in a DO4 type package designed with very low leakage current as well as good surge handling capability. These devices are ideal for use in applications where economy, power capability, and reliability are demanding considerations.

Ratings and Characteristics:

Peak Reverse Voltage, P_{RV}	
NTE5864, NTE5865*	200V
NTE5884, NTE5885*	600V
NTE5888, NTE5889*	1200V
Maximum Forward Current (Single Phase, Half Wave, T_C = +121°C), $I_{F(AV)}$	30A
Maximum Forward Surge Current (Single Cycle Amps), I_{FSM}	300A
Maximum Forward Voltage Drop (I_O = 30A, T_C = +25°C), V_F	1.2V
Maximum Reverse Current (FCA at +150°C), I_R	1mA
Fusing Current (Less than 8ms), I^2t	$350A^2s$
Reverse Power for Bulk Avalanche	0.16 Joules
Operating Temperature Range, T_{opr}	–40° to +175°C
Storage Temperature Range, T_{stg}	–55° to +190°C
Maximum Thermal Resistance, Junction–to–Case, R_{thJC}	3.0°C/W

Note 1. Standard polarity is cathode to case, (*) indicated anode to case.